

# MA2Z748

## Silicon epitaxial planar type

For super-high speed switching circuit

For small current rectification

### ■ Features

- Low  $V_F$  type of MA2Z720
- High rectification efficiency caused by its low forward-rise-voltage ( $V_F$ )
- Optimum for high-frequency rectification because of its short reverse recovery time ( $t_{rr}$ )

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	20	V
Repetitive peak reverse voltage	$V_{RRM}$	20	V
Average forward current	$I_{F(AV)}$	300	mA
Non-repetitive peak forward surge current*	$I_{FSM}$	3	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note) \* : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

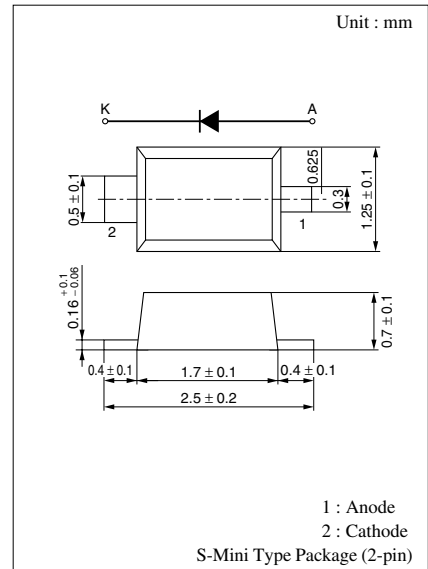
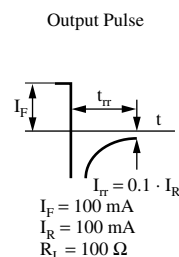
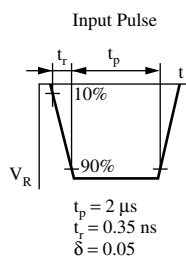
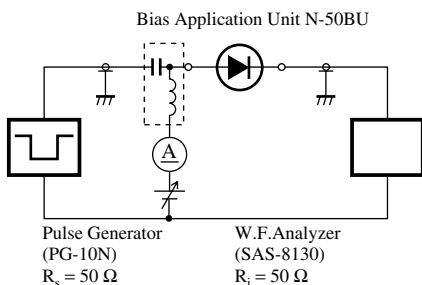
### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 10\text{ V}$			30	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 300\text{ mA}$			0.4	V
Terminal capacitance	$C_t$	$V_R = 0\text{ V}, f = 1\text{ MHz}$		60		pF
Reverse recovery time*	$t_{rr}$	$I_F = I_R = 100\text{ mA}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100\ \Omega$		5		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 400 MHz

3. \*:  $t_{rr}$  measuring instrument



Marking Symbol: 2K

Internal Connection

